

# BRCS050N04DP

Rev.A Mar.-2026

## 描述 / Descriptions

TO-252 塑封封装 N 沟道 MOS 场效应管。  
N-CHANNEL MOSFET in a TO-252 Plastic Package.

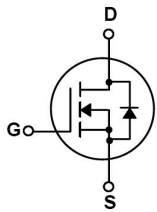
## 特征 / Features

$V_{DS} = 40V$       $I_D = 78A$  ( $V_{GS} = \pm 20V$ )  
 $R_{DS(ON)}@10V \leq 5.5m\Omega$  (Typ.  $4.9m\Omega$ )  
 $R_{DS(ON)}@4.5V \leq 10m\Omega$  (Typ.  $6.6m\Omega$ )  
 无卤产品。HF Product.

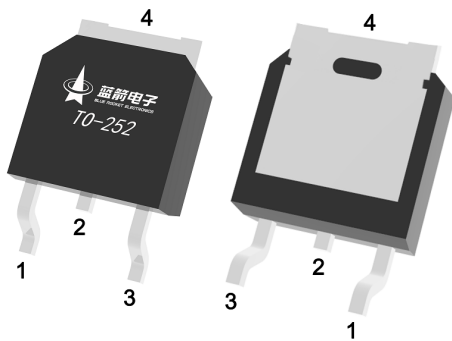
## 用途 / Applications

用于高功率 DC/DC 转换和功率开关。  
 These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN 1 : G     PIN 2 : D     PIN 3 : S     PIN 4 : D

## 印章代码 / Marking

见印章说明。  
 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Drain Current	I <sub>D</sub> (Tc=25°C)	78	A
Drain Current - Pulsed	I <sub>DM</sub>	174	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Single Pulsed Avalanche Energy	E <sub>AS</sub>	841	mJ
Avalanche Current	I <sub>AS</sub>	29	A
Power Dissipation	P <sub>D</sub> (Tc=25°C)	55	W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C
Junction-to-Ambient	t ≤ 10	20	°C/W
Junction-to-Ambient	Steady-State	50	
Junction-to-Case	Steady-State	2.27	

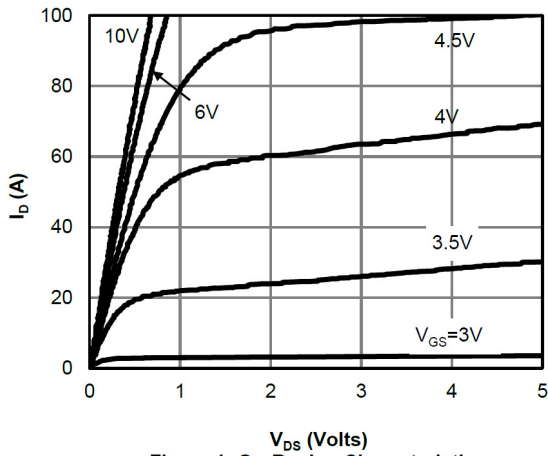
**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	48.5		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current Forward	I <sub>GSS</sub>	V <sub>GS</sub> =±20V V <sub>DS</sub> =0V			±0.1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1.0	1.4	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V I <sub>D</sub> =20A		4.9	5.5	mΩ
		V <sub>GS</sub> =4.5V I <sub>D</sub> =10A		6.6	10	mΩ
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V I <sub>S</sub> =1A			1.2	V
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1.0MHz		3220		pF
Output Capacitance	C <sub>oss</sub>			215		
Reverse Transfer Capacitance	C <sub>rss</sub>			190		
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V V <sub>DS</sub> =0V f=1MHz		2.3		Ω
Total Gate Charge	Q <sub>g(10V)</sub>	V <sub>GS</sub> =10V V <sub>DS</sub> =20V I <sub>D</sub> =10A		59.1		nC
Total Gate Charge	Q <sub>g(4.5V)</sub>			28.3		
Gate Source Charge	Q <sub>gs</sub>			5.4		
Gate Drain Charge	Q <sub>gd</sub>			10.0		

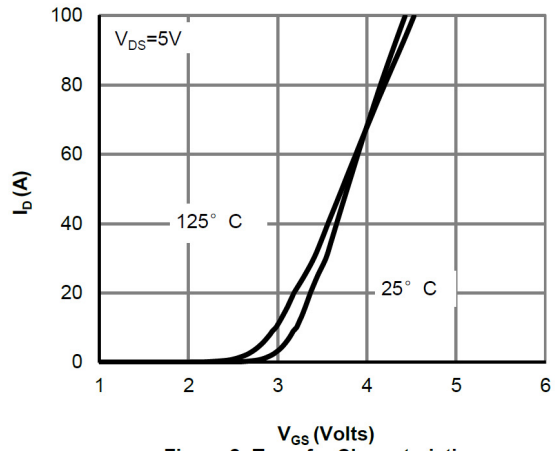
## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $I_D=10A$ $R_g=3\Omega$		11.8		ns
Turn-On Rise Time	$t_r$			15.1		
Turn-Off Delay Time	$t_{d(off)}$			57.6		
Turn-Off Fall Time	$t_f$			16.9		

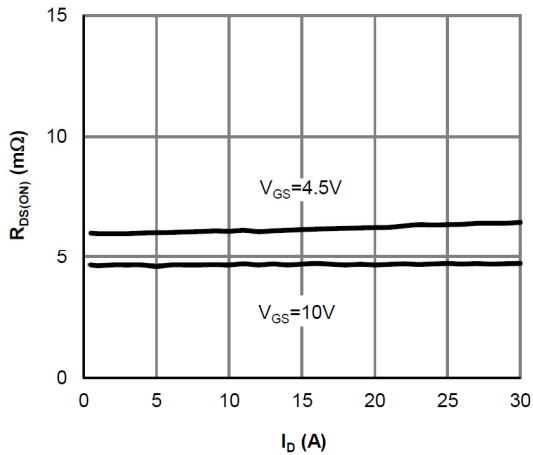
**电参数曲线图 / Electrical Characteristic Curve**



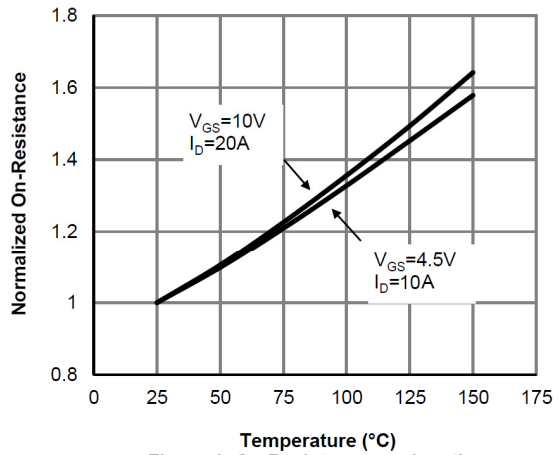
**Figure 1: On-Region Characteristics**



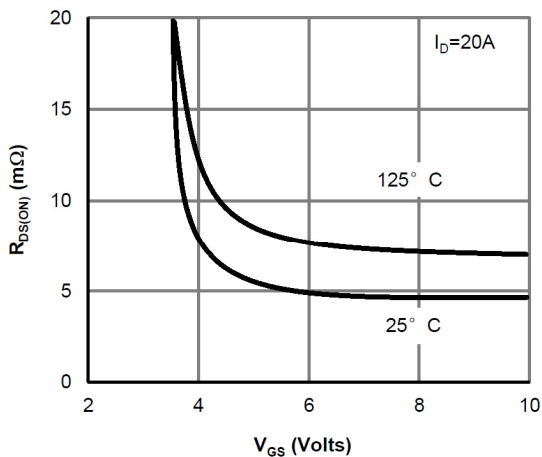
**Figure 2: Transfer Characteristics**



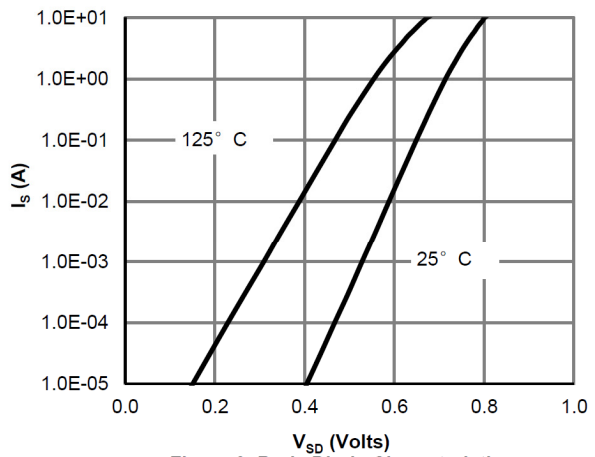
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



**Figure 5: On-Resistance vs. Gate-Source Voltage**



**Figure 6: Body-Diode Characteristics**

## 电参数曲线图 / Electrical Characteristic Curve

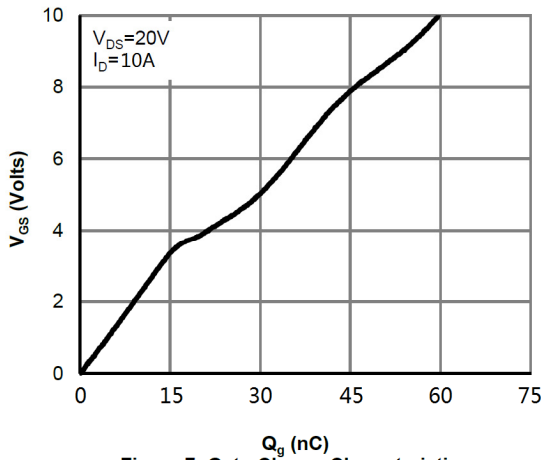


Figure 7: Gate-Charge Characteristics

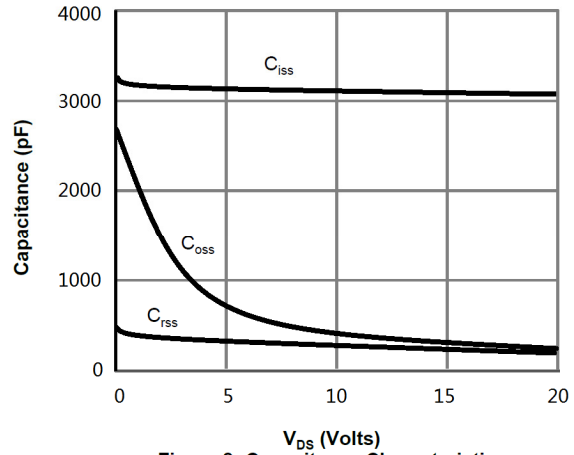


Figure 8: Capacitance Characteristics

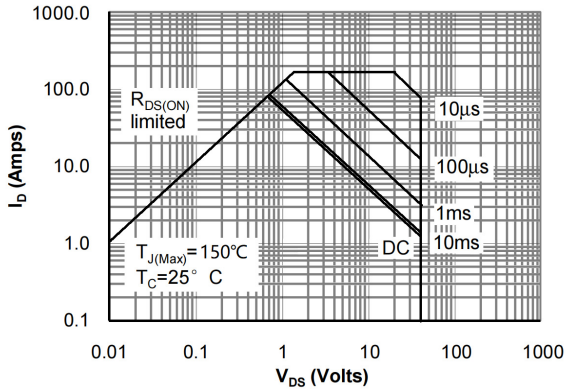


Figure 9: Maximum Forward Biased Safe Operating Area

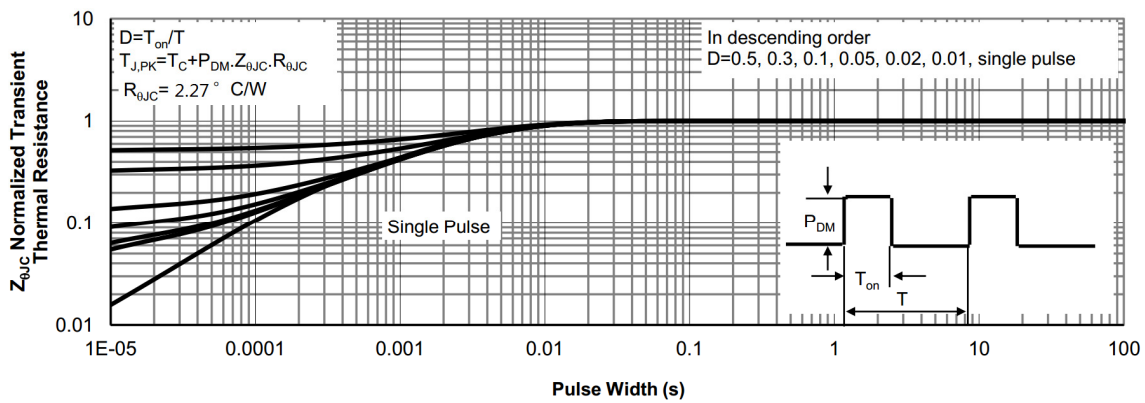
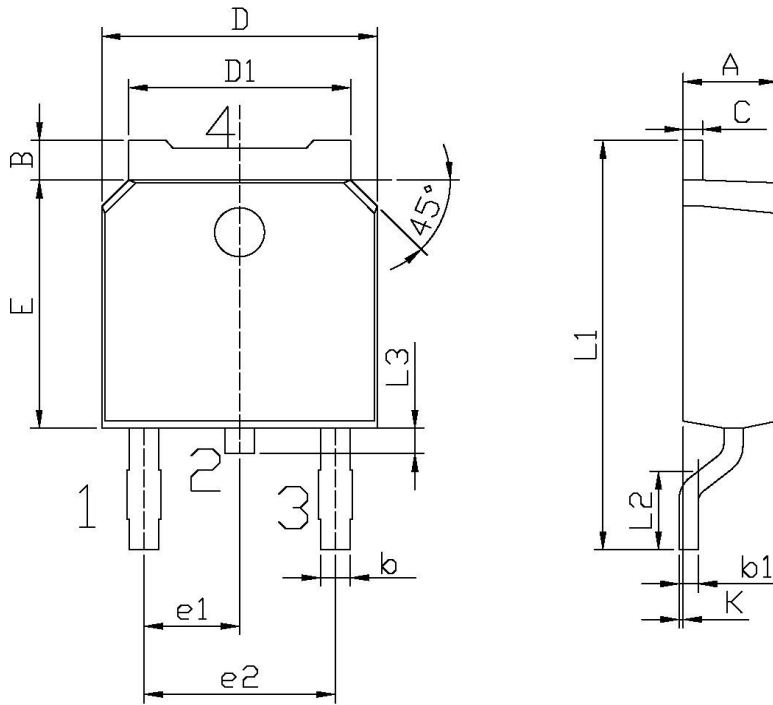


Figure 10: Normalized Maximum Transient Thermal Impedance

**外形尺寸图 / Package Dimensions**

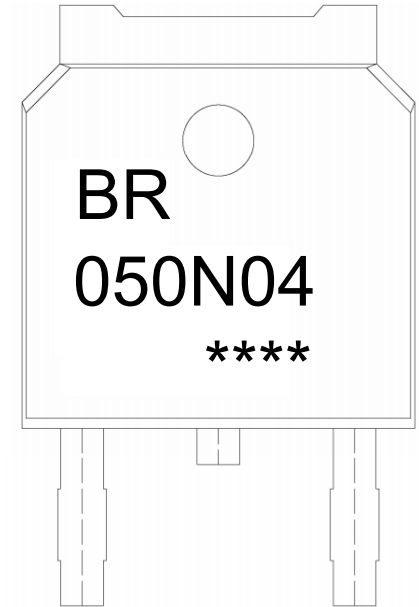


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

**印章说明 / Marking Instructions**



说明：

BR： 为公司代码

050N04： 为产品型号

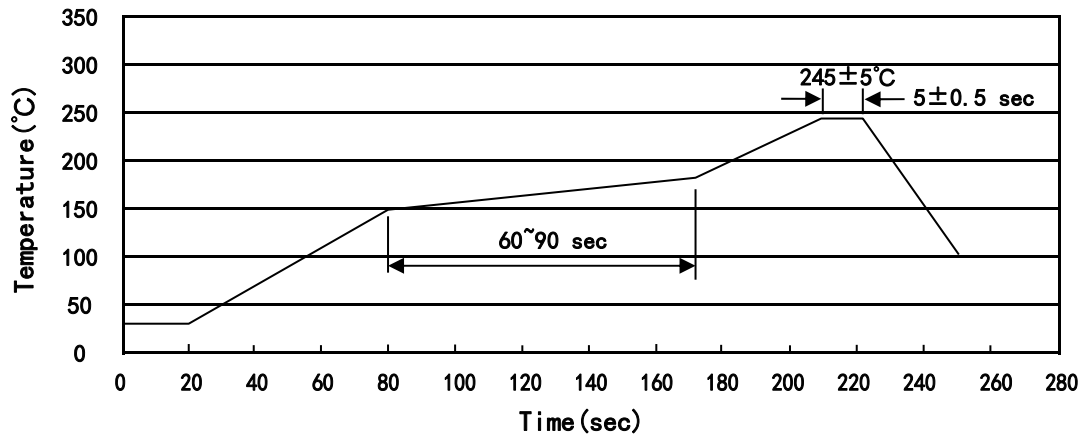
\*\*\*\*： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

050N04: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No.

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

**使用说明 / Notices**

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